



PROTON

JSC “Proton”

MOSFET chip DMOST222

Description

MOSFET chip with internal channel (normally-on)
DMOST222 is designed to be used in hybrid microchips and packaged field-effect transistors.

Features

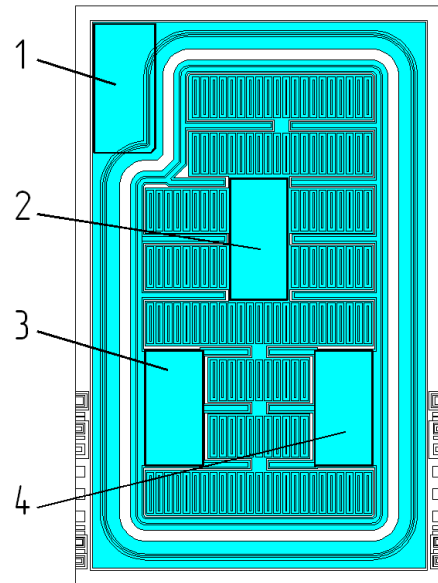
- Chip size — 1.01 x 1.6 mm
- Chip thickness – 0.36±0.02 mm
- Metallization: top – AlSi, bottom – Si

Absolute maximum ratings

Maximum Temperature	
Storage Temperature	- 60 °C to 150 °C
Operating Junction Temperature	- 60 °C to 125 °C
Maximum Voltage	
Drain-to-Source Voltage	230 V
Gate-to-Source Voltage	- 35 V

Contact pads size

Pad #	X, mm	Y, mm	Pad #	X, mm	Y, mm
1	0.17	0.36	3	0.16	0.32
2	0.16	0.33	4	0.16	0.32



- 1 – Drain
- 2 – Gate
- 3 – Source
- 4 – Source

Electrical characteristics (T = 25 °C)

Parameter	Symbol	Unit	Min.	Typ.	Max.	Conditions
Drain-to-Source ON-State Resistance	R_{DS}	Ohm			15	$V_{GS} = 0 \text{ V}, I_D = 100 \text{ mA}$
Drain Leakage Current	$I_{LEAK.D}$	μA			1.0	$V_{GS} = -4 \text{ V}, V_{DS} = 230 \text{ V}$
Gate Leakage Current	$I_{LEAK.G}$	μA			0.1	$V_{GS} = -35 \text{ V}, V_{DS} = 0 \text{ V}$
LED Constant Forward Voltage (drain ⁻ , source ⁺)	V_{SD}	V			0.95	$V_{GS} = -4.5 \text{ V}, I_D = 150 \text{ mA}$
Drain Saturation Current	$V_{SAT.D}$	mA	160			$V_{GS} = -0.5 \text{ V}, V_{DS} = 5 \text{ V}$
					280	$V_{GS} = -0.5 \text{ V}, V_{DS} = 8 \text{ V}$